The Influence of silane gas flow rate on optoelectronic properties of Uc-Si: H Prepared by HWC-VHF-PECVD Technique

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Abstrak

Hydrogenated microcrystalline silicon (Uc-Si:H) thin films have been deposited using 10 % silane (SiH_4) in H_2 dilution by Hot Wire Cell Very High Frequency Plasma Enhanced Chemical Vapor Deposition (HWC-VHF-PECVD) technique.....